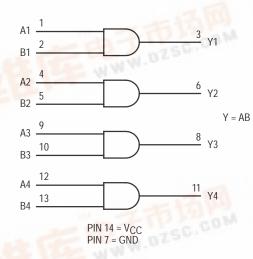
Quad 2-Input AND Gate

High-Performance Silicon-Gate CMOS

The MC74HC08A is identical in pinout to the LS08. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 24 FETs or 6 Equivalent Gates

LOGIC DIAGRAM



Pinout: 14-Lead Packages (Top View)



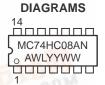


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http://onsemi.com



PDIP-14 N SUFFIX CASE 646



MARKING



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location
WL or L = Wafer Lot
YY or Y = Year

WW or W = Work Week

FUNCTION TABLE

| Inputs | | Output | | | | |
|--------|---|--------|--|--|--|--|
| Α | В | Υ | | | | |
| L | L | L | | | | |
| L | Н | L | | | | |
| Н | L | - 5 | | | | |
| H | H | Н | | | | |
| DZSG-W | | | | | | |
| | | | | | | |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------------|----------|-------------|
| MC74HC08AN | PDIP-14 | 2000 / Box |
| MC74HC08AD | SOIC-14 | 55 / Rail |
| MC74HC08ADR2 | SOIC-14 | 2500 / Reel |
| MC74HC08ADT | TSSOP-14 | 96 / Rail |
| MC74HC08ADTR2 | TSSOP-14 | 2500 / Reel |



MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------|------|
| VCC | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| l _{in} | DC Input Current, per Pin | ± 20 | mA |
| l _{out} | DC Output Current, per Pin | ± 25 | mA |
| ICC | DC Supply Current, V_{CC} and GND Pins | ± 50 | mA |
| PD | Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package† | 750 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | | Max | Unit |
|------------------------------------|--|---|-------------|--------------------|------|
| VCC | DC Supply Voltage (Referenced to GND) | | | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | | | Vcc | V |
| TA | Operating Temperature, All Package Types | | | + 125 | °C |
| t _r , t _f | (Figure 1) \ | / _{CC} = 2.0 V / _{CC} = 4.5 V / _{CC} = 6.0 V | 0 0 0 | 1000 500 400 | ns |

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/ $^{\circ}$ C from 65 $^{\circ}$ to 125 $^{\circ}$ C

DC CHARACTERISTICS (Voltages Referenced to GND)

| | | | VCC | Guara | nteed Lim | nit | |
|-----------------|---|---|--------------------------|------------------------------|------------------------------|------------------------------|------|
| Symbol | Parameter | Condition | v | –55 to 25°C | ≤85°C | ≤125°C | Unit |
| VIH | Minimum High-Level Input Voltage | $V_{out} = 0.1V \text{ or } V_{CC} -0.1V$ $ I_{out} \le 20 \mu A$ | 2.0 3.0 4.5 6.0 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | 1.50 2.10 3.15 4.20 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{out} = 0.1V \text{ or } V_{CC} - 0.1V$ $ I_{out} \le 20\mu\text{A}$ | 2.0 3.0 4.5 6.0 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | 0.50 0.90 1.35 1.80 | V |
| VOH | Minimum High-Level Output Voltage | V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20μA | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $ \begin{array}{c cccc} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4\text{mA} \\ & I_{out} \leq 4.0\text{mA} \\ & I_{out} \leq 5.2\text{mA} \end{array} $ | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | |
| VOL | Maximum Low–Level Output Voltage | V _{in} = V _{IH} or V _{IL} I _{Out} ≤ 20μΑ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $V_{in} = V_{IH} \text{ or } V_{IL} \qquad \begin{aligned} I_{out} &\leq 2.4 \text{mA} \\ I_{out} &\leq 4.0 \text{mA} \\ I_{out} &\leq 5.2 \text{mA} \end{aligned}$ | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ±0.1 | ±1.0 | ±1.0 | μΑ |
| lcc | Maximum Quiescent Supply Current (per Package) | V _{in} = V _{CC} or GND I _{out} = 0µA | 6.0 | 1.0 | 10 | 40 | μА |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50pF$, Input $t_f = t_f = 6ns$)

| | | VCC | Guaranteed Limit | | | |
|--|---|--------------------------|----------------------|----------------------|-----------------------|------|
| Symbol | Parameter | V | –55 to 25°C | ≤85°C | ≤125°C | Unit |
| tPLH, tPHL | Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 2) | 2.0 3.0 4.5 6.0 | 75 27 15 13 | 95 32 19 16 | 110 36 22 19 | ns |
| C _{in} | Maximum Input Capacitance | | 10 | 10 | 10 | pF |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V, V _{EE} = 0 V | | |
|----------|---|--|----|---|
| C_{PD} | Power Dissipation Capacitance (Per Buffer)* | 20 | pF | l |

^{*}Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

http://opsomi.com

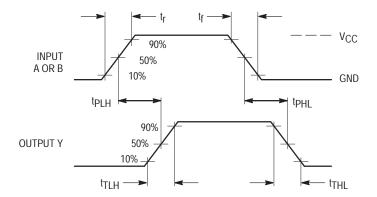
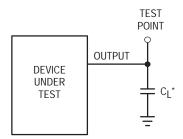


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

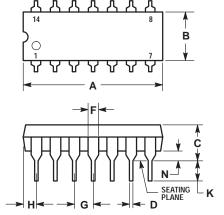
Figure 2. Test Circuit



Figure 3. Expanded Logic Diagram (1/4 of the Device)

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L





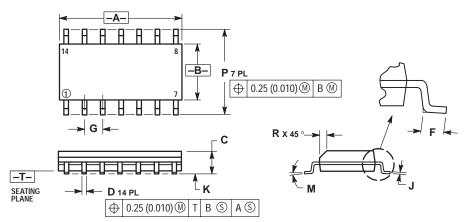
- NOTES:

 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.

 2. DIMENSION L. TO CENTER OF LEADS WHEN
- FORMED PARALLEL.
 3. DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.
 4. ROUNDED CORNERS OPTIONAL.

| | INC | HES | MILLIN | IETERS |
|-----|-------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.715 | 0.770 | 18.16 | 19.56 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| С | 0.145 | 0.185 | 3.69 | 4.69 |
| D | 0.015 | 0.021 | 0.38 | 0.53 |
| F | 0.040 | 0.070 | 1.02 | 1.78 |
| G | 0.100 | BSC | 2.54 | BSC |
| Н | 0.052 | 0.095 | 1.32 | 2.41 |
| J | 0.008 | 0.015 | 0.20 | 0.38 |
| K | 0.115 | 0.135 | 2.92 | 3.43 |
| L | 0.300 | BSC | 7.62 BSC | |
| M | 0° | 10° | 0° | 10° |
| N | 0.015 | 0.039 | 0.39 | 1.01 |

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



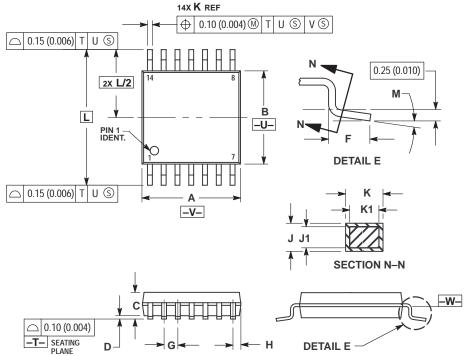
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIN | METERS | INC | HES |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 8.55 | 8.75 | 0.337 | 0.344 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 | BSC | 0.050 BSC | |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0 ° | 7° | 0° | 7° |
| Р | 5.80 | 6.20 | 0.228 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINIAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

| | MILLIMETERS | | INC | HES | |
|-----|-------------|------|-------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 4.90 | 5.10 | 0.193 | 0.200 | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | |
| С | | 1.20 | | 0.047 | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | |
| G | 0.65 | BSC | 0.026 | BSC | |
| Н | 0.50 | 0.60 | 0.020 | 0.024 | |
| J | 0.09 | 0.20 | 0.004 | 0.008 | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | |
| K | 0.19 | 0.30 | 0.007 | 0.012 | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | |
| L | 6.40 BSC | | 0.252 | | |
| M | 0° | 8° | 0° | 8° | |

Notes

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